What is claimed is:

1. A method of forming an electronic device, the method comprising:

forming a graphene barrier layer on a substrate surface, the graphene barrier layer formed by a method comprising plasma enhanced atomic layer deposition; and

depositing a fill layer over the graphene barrier layer,

wherein the graphene barrier layer prevents diffusion of at least one element between the fill layer and the substrate surface.

2. The method of claim 1, wherein the substrate surface comprises a dielectric material.

3. The method of claim 2, wherein the dielectric material comprises a metal oxide.

4. The method of claim 2, wherein the dielectric material consists essentially of Al_2O_3.

5. The method of claim 1, wherein the graphene barrier layer has a thickness in a range of 15 Å to 100 Å.

6. The method of claim 1, wherein the fill layer comprises one or more of tungsten, ruthenium, copper, or cobalt.

7. The method of claim 1, wherein the at least one element comprises one or more of a halogen, oxygen or boron.

8. The method of claim 7, wherein the at least one element comprises fluorine.

9. The method of claim 1, wherein the fill layer comprises tungsten and the fill layer is deposited by a method comprising:

forming an amorphous silicon layer on the graphene barrier layer; and

exposing the amorphous silicon layer to a tungsten precursor to form a tungsten layer by atomic substitution.

10. The method of claim 9, wherein the tungsten precursor comprises WF_6 and the at least one element comprises fluorine.

11. The method of claim 1, wherein the fill layer comprises tungsten and the fill layer is deposited by a method comprising sequentially exposing the graphene barrier layer to a tungsten precursor comprising WF_6 and a reactant.

12. A method of forming an electronic device, the method comprising:

forming a graphene barrier layer on a substrate surface comprising Al_2O_3;

forming an amorphous silicon layer on the graphene barrier layer; and

exposing the amorphous silicon layer to a tungsten precursor to form a tungsten layer by atomic substitution, the tungsten precursor comprising WF_6,

wherein the graphene barrier layer prevents diffusion of fluorine into the substrate surface.

13. An electronic device comprising a graphene barrier layer between a first material and a second material, wherein the graphene barrier layer prevents diffusion of at least one element between the first material and the second material, wherein the device is a 3D NAND device comprising a plurality of alternating layers of the first material and the second material.

14. The device of claim 13, wherein the graphene barrier layer has a thickness in a rage of 15 Å to 100 Å.

15. The device of claim 13, wherein the at least one element comprises one or more of a halogen, oxygen or boron.

16. The device of claim 15, wherein the at least one element comprises fluorine.

17. The device of claim 13, wherein the first material comprises tungsten and the second material comprises Al_2O_3.

18. The device of claim 17, the at least one element comprises fluorine.